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Docket No.: 071971-0643

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| In re Application of | : | Customer Number: 53080 |
| Shunsaku MURAOKA, et al. | : | Confirmation Number: 5602 |
| Application No.: 10/584,617 | : | Group Art Unit: 2824 |
| Filed: June 26, 2006 | : | Examiner: NGUYEN, NAM THANH |
| For: MEMORY DEVICE, MEMORY CIRCUIT AND SEMICONDUCTOR INTEGRATED CIRCUIT HAVING VARIABLE RESISTANCE | : | |

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

This Information Disclosure Statement is being filed more than three months after the U.S. filing date and after the mailing date of a Final Rejection or Notice of Allowance, but before payment of the Issue Fee.

**REQUEST TO CONSIDER REFERENCES AFTER CLOSE OF PROSECUTION AND
BEFORE PAYMENT OF ISSUE FEE**

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear

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among the "References Cited" on any patent to issue therefrom. Please charge the processing fee under 1.17(p) of \$180.00 to Deposit Account 500417.

CERTIFICATION PARAGRAPH

The undersigned certifies that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement as described in 37 CFR 1.97(e)(1).

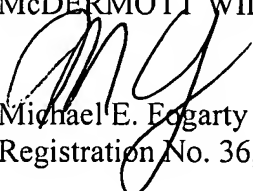
The reference **WO 03/041172 A1** was cited in a corresponding Korean Office Action and its relevance is discussed therein. A copy of the Korean Office Action is attached for the Examiner's information.

Please note the article "**Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)**" listed on the attached Korean Office Action was previously submitted to the U.S. Patent and Trademark Office on April 11, 2008.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Please recognize our Customer No. 53080
as our correspondence address.**